
The distribution of minority carriers in semi-infinite semiconductor material with defects on the surface after their diffusion from a thin planar source

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The article considers application of mathematical modeling methods for solving the problem of diffusion of minority carriers (MC), generated in the semiconductor by wide electron beam. The influence of defects on the semiconductor surface on the distribution of MC after their diffusion from a thin planar source into a semi-infinite semiconductor was investigated. The calculations were performed for various materials of semiconductor electronics.

Keywords: *distribution of minority carriers, defect, semiconductor materials, electron beam.*

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